

**MATERIALS RESEARCH SOCIETY**  
**SYMPOSIUM PROCEEDINGS VOLUME 1731**

# **Oxide Semiconductors**

November 30 – December 5, 2014  
Boston, Massachusetts, USA

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Curran Associates, Inc.  
57 Morehouse Lane  
Red Hook, NY 12571  
[www.proceedings.com](http://www.proceedings.com)

**ISBN: 978-1-5108-0612-2**

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Cambridge, New York, Melbourne, Madrid, Cape Town,  
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Cambridge University Press  
32 Avenue of the Americas, New York, NY 10013-2473, USA  
[www.cambridge.org](http://www.cambridge.org)

Materials Research Society  
506 Keystone Drive, Warrendale, PA 15086  
[www.mrs.org](http://www.mrs.org)

CODEN: MRSPDH

ISBN: 978-1-5108-0612-2

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